

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Guaranteed avalanche
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS											
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS							
Cathode to anode voltage	V _{RRM}		600	V							
Maximum continuous forward current	I _F	T _C = 100 °C	8								
Single pulse forward current	I _{FSM}		60	A							
Peak repetitive forward current	I _{FRM}		24								
Maximum power dissipation	PD	T _C = 100 °C	14	W							
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C							

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
Forward voltage		I _F = 8 A		-	1.4	1.7	V			
	V _F	I _F = 16 A	See fig. 1	-	1.7	2.1				
		I _F = 8 A, T _J = 125 °C		-	1.4	1.7				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.3	5.0	μA				
leakage current	IR	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	100	500					
Junction capacitance	CT	V _R = 200 V	-	10	25	pF				
Series inductance	Ls	Measured lead to lead 5 mm from page	ckage body	-	8.0	-	nH			

Revision: 22-Jun-15

Document Number: 94042

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

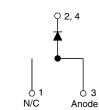
1

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A

PRODUCT SUMMARY	
Package	TO-252AA (D-PAK)
I _{F(AV)}	8 A
V _R	600 V
V_F at I_F	1.4 V
t _{rr} typ.	18 ns
T _J max.	150 °C

www.vishay.com





Single die

TO-252AA (D-PAK)

Diode variation

Vishay Semiconductors

ROHS COMPLIANT



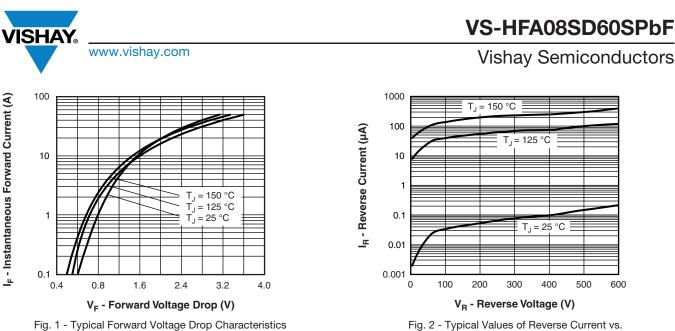


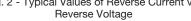
www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			-				
	t _{rr}	T _J = 25 °C		-	37	55	ns			
		T _J = 125 °C	I _F = 8 A dI _F /dt = 200 A/µs V _R = 200 V	-	55	90				
Deal and a second	I _{RRM}	T _J = 25 °C		-	3.5	5.0	A nC			
Peak recovery current		T _J = 125 °C		-	4.5	8.0				
Poverse recovery charge	Q _{rr}	T _J = 25 °C		-	65	138				
Reverse recovery charge		T _J = 125 °C		-	124	360				
Rate of fall of recovery current	dl _{(rec)M} /dt	T _J = 25 °C		-	240	-				
		T _J = 125 °C		-	210	-	A/µs			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	3.5	°C/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	0/00				
Weight			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Marking device		Case style D-PAK		HFA08	SD60S					





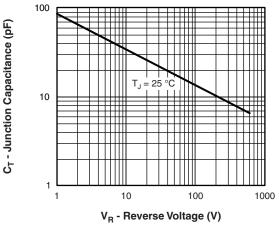


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

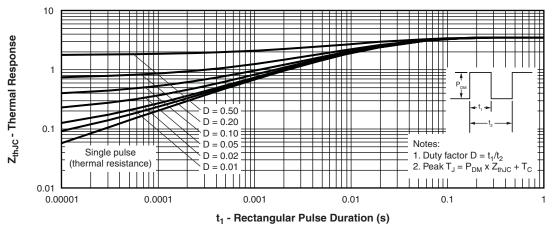


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



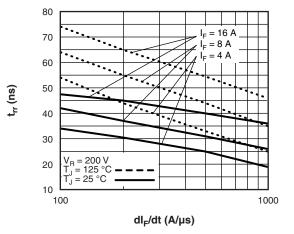


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

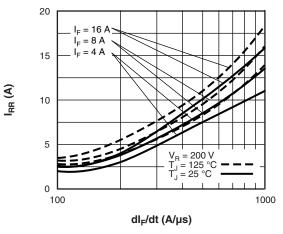
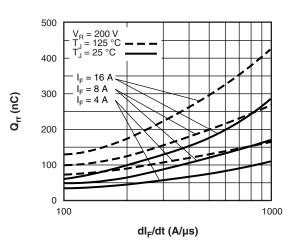
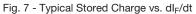


Fig. 6 - Typical Recovery Current vs. dl_F/dt

VS-HFA08SD60SPbF

Vishay Semiconductors





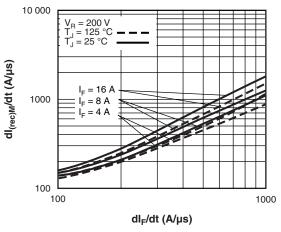


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

Revision: 22-Jun-15 4 Document Number: 94042 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-HFA08SD60SPbF



Vishay Semiconductors

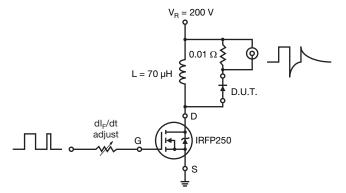
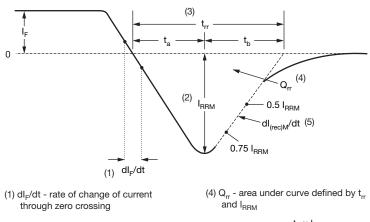


Fig. 9 - Reverse Recovery Parameter Test Circuit



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



- (5) dI_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions



Vishay Semiconductors



ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	08	SD	60	S	TR	PbF			
		2	3	4	5	6	(7)	8	9			
	 Vishay Semiconductors product HEXFRED[®] family 											
	2 - 3 -		tron irra	-								
	4 -	Curr	ent ratir	ng (08 =	8 A)							
	5 -	D-P/	٩K									
	6 -	Volta	age ratir	ng (60 =	600 V)							
	7 -	S =	D-PAK									
	8 - • TR = tape and reel											
	 TRR = tape and reel (right oriented) 											
	 TRL = tape and reel (left oriented) 											
	9 -	• Pb	F = lead	l (Pb)-fr	ee							
		• P =	= lead (F	Pb)-free	(for TRI	R and T	RL)					

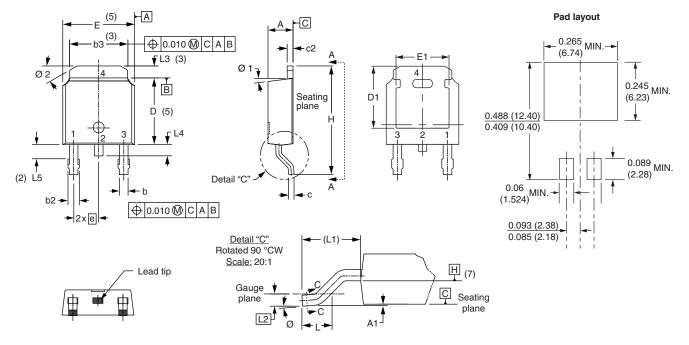
LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95016							
Part marking information	www.vishay.com/doc?95059							
Packaging information	www.vishay.com/doc?95033							





D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NUTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090) BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3		L2 0.51 BSC 0.020 BSC		BSC			
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5]	Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

(2) Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA

Document Number: 95016



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.